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Growing Method		
/	Dopant/Model	Ga/P
Oxygen Content		
		$\leq 7.5 \times 10^3$ atoms/cm ³ 15ppma
Carbon Content		
		$\leq 5.0 \times 10^3$ atoms/cm ³ 1ppma
Dislocation Density		
		≤ 500 pcs/cm ²
Crystal Orientation		

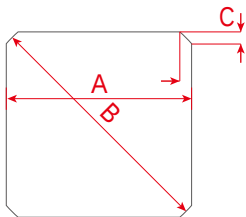
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Resistivity		0.4~1.1Ω.cm
Minm		≥80μ

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Square		
Right Angle		
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owing	\$	±10μm
Diamond Wire Slicing		



Size G12
A 210±0.25mm
B 295±0.25mm
C 1.41±0.45mm